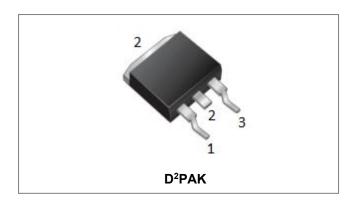


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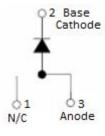
SDURB860A ULTRAFAST RECTIFIER



Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- · Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- This is a Pb free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	600	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=100°C, rectangular wave form	8	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	110	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 8A, Pulse, T _J = 25°C	1.7	2.0	V
Reverse Current*	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25^{\circ}C$	0.5	8	μA
	I _{R2}	@ V_R = rated V_R T_J = 125°C	0.2	1	mA
Reverse Recovery Time	t _{rr}	I _F =500mA, I _R =1A,and I _{rm} =250mA	32	35	ns

^{*} Pulse width < 300 µs, duty cycle < 2%

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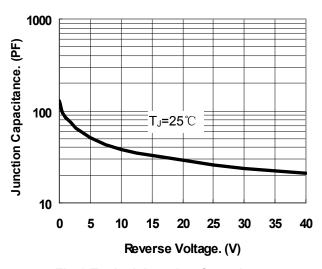




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	R ₀ JA	DC operation	25	°C/W
Approximate Weight	wt	-	1.85	g
Case Style	D ² PAK			

Ratings and Characteristics Curves



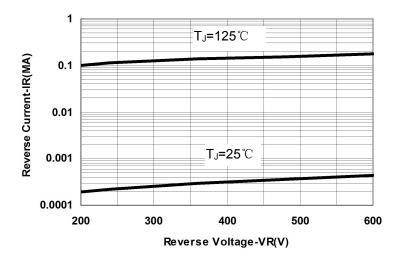


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

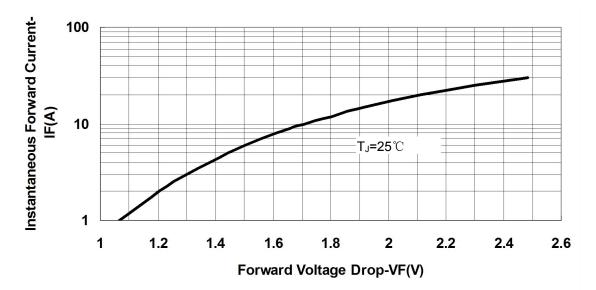


Fig.3-Typical Forward Voltage Drop Characteristics

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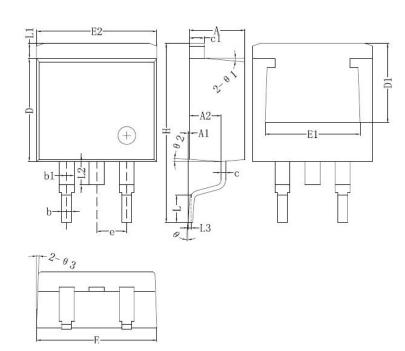


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Mechanical Dimensions D²PAK



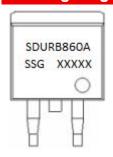
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
Α	4.47	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
С	0.31	0.38	0.61
c1	1.17	1.27	1.37
D	8.50	8.70	8.90
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.31
е		2.54	
Н	14.6	15.1	15.6
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	1.30		2.20
L3		0.25BSC	
е	0	-	8°
e1		5°	
e2		4°	
e3		4°	

Ordering Information

Device	Package	Shipping
SDURB860A	D ² PAK	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

 SDUR
 = Device Type

 B
 = Package type

 8
 = Forward Current (8A)

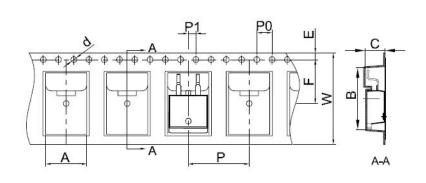
 60
 = Reverse Voltage(600V)

 Δ
 = Δ

A = A SSG = SSG YY = Year WW = Week L = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification D²PAK



CVMDOL	Millimeters		
SYMBOL	Min.	Max.	
Α	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	

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SDURB860A



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